



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:  
Latchford, et al.

Serial No.: 09/921,938

Confirmation No.: 8367

Filed: August 2, 2001

## For: Photolithography Scheme Using a Silicon Containing Resist

**Box AF**  
Assistant Commissioner for Patents  
Washington, D.C. 20231

**CERTIFICATE OF MAILING**  
**37 CFR 1.8**

Dear Sir:

**RESPONSE FINAL TO OFFICE ACTION DATED MAY 6, 2002**

In response to the Final Office Action dated May 6, 2002, having a shortened statutory period for response extend one-month to expire on September 6, 2002, Applicant requests entry and consideration of the following remarks. Although Applicant believes that no fee is due in conjunction with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/AMAT/4227.P1/DSM/BCVD/KMT, for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

## In The Claims:

Please amend the claims as follows:

1. (Amended) A method for forming a patterned amorphous carbon layer in a multilayer stack, comprising:
  - depositing an amorphous carbon layer on a substrate;
  - depositing a silicon containing photoresist layer on top of the amorphous carbon layer;